

BUK9832-55A

N-channel TrenchMOS logic level FET Rev. 02 — 1 June 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Suitable for logic level gate drive sources

Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference da	ta				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{sp} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	12	A
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	8	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A};$ $T_j = 25 \text{ °C}$	-	-	36	mΩ
	resistance	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 8 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$	-	25	29	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	27	32	mΩ
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 10 \text{ A}; V_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{unclamped} \end{split} $	-	-	100	mJ

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain		
3	S	source		
4	D	drain		G THE
				mbb076 S
			SOT223 (SC-73)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK9832-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

100

-

mJ

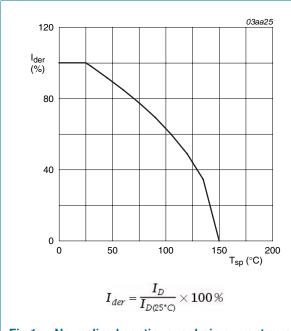
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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	-	55	V
V _{GS}	gate-source voltage		-10	-	10	V
I _D	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$ see $\frac{\text{Figure 3}}{\text{Figure 3}}$	-	-	12	A
		$T_{sp} = 100 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{1}$	-	-	7	А
I _{DM}	peak drain current	$T_{sp} = 25 \text{ °C; } t_p \le 10 \mu s; \text{ pulsed;}$ see <u>Figure 3</u>	-	-	47	A
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	8	W
T _{stg}	storage temperature		-55	-	150	°C
Tj	junction temperature		-55	-	150	°C
V _{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \ \mu s$	-15	-	15	V
Source-drai	n diode					
Is	source current	T _{sp} = 25 °C	-	-	12	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{sp} = 25 \ ^{\circ}C$	-	-	47	А
Avalanche r	uggedness					

E_{DS(AL)S} non-repetitive drain-source avalanche energy 

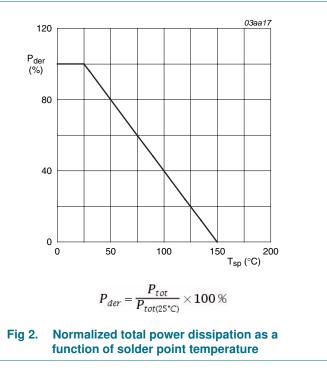


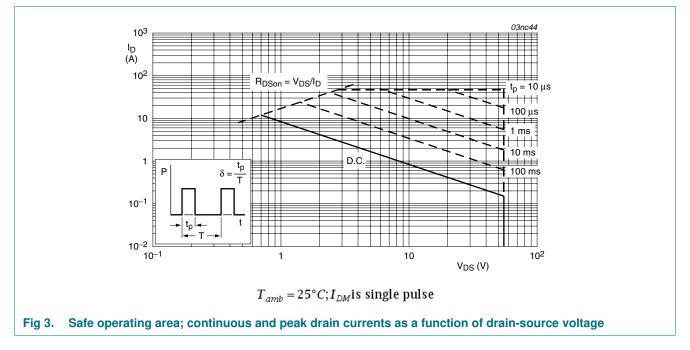
Fig 1. Normalized continuous drain current as a function of solder point temperature

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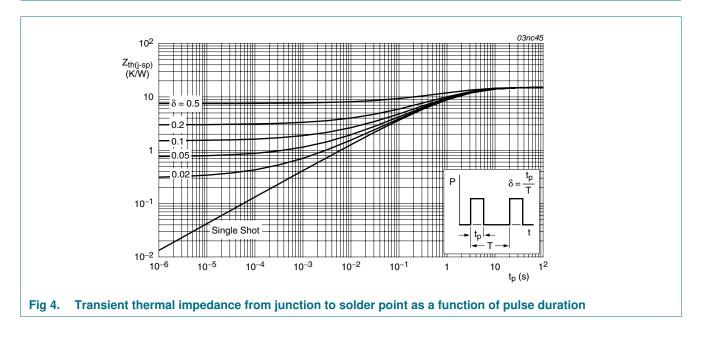
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	see <u>Figure 4</u>	-	70	-	K/W

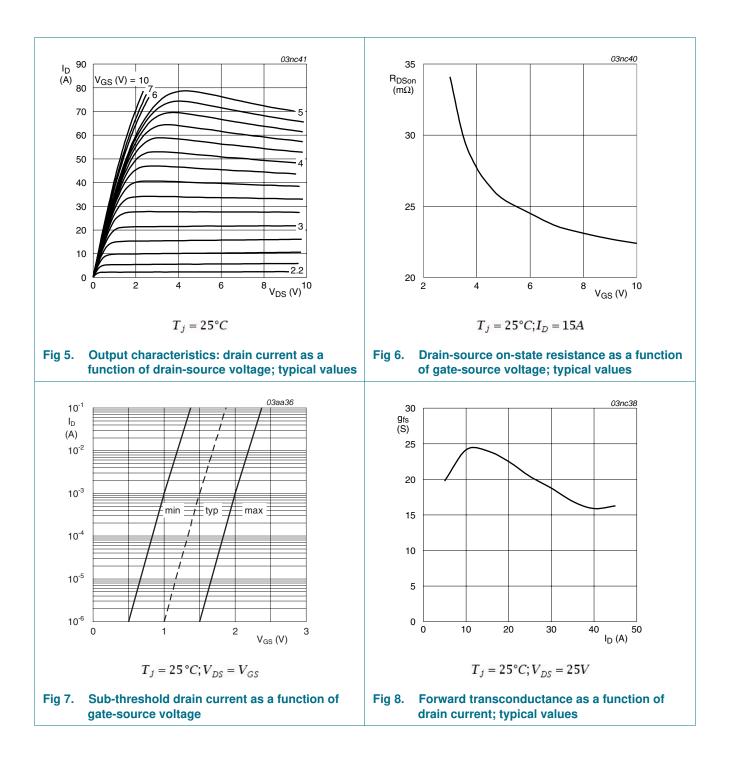


6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	BR)DSS drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	2.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; see <u>Figure 11</u>	0.6	-	-	V
I _{DSS} drain leakage cu	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	500	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 10 V; T _j = 25 °C	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon} drain-source or resistance	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ °C}$	-	-	36	mΩ
	resistance	V _{GS} = 5 V; I _D = 8 A; T _j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	59	mΩ
		V_{GS} = 10 V; I _D = 8 A; T _j = 25 °C	-	25	29	mΩ
		V _{GS} = 5 V; I _D = 8 A; T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	27	32	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1195	1594	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	212	254	pF
C _{rss}	reverse transfer capacitance		-	144	198	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	125	-	ns
t _{d(off)}	turn-off delay time		-	64	-	ns
t _f	fall time		-	68	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 18 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	51	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	80	-	nC

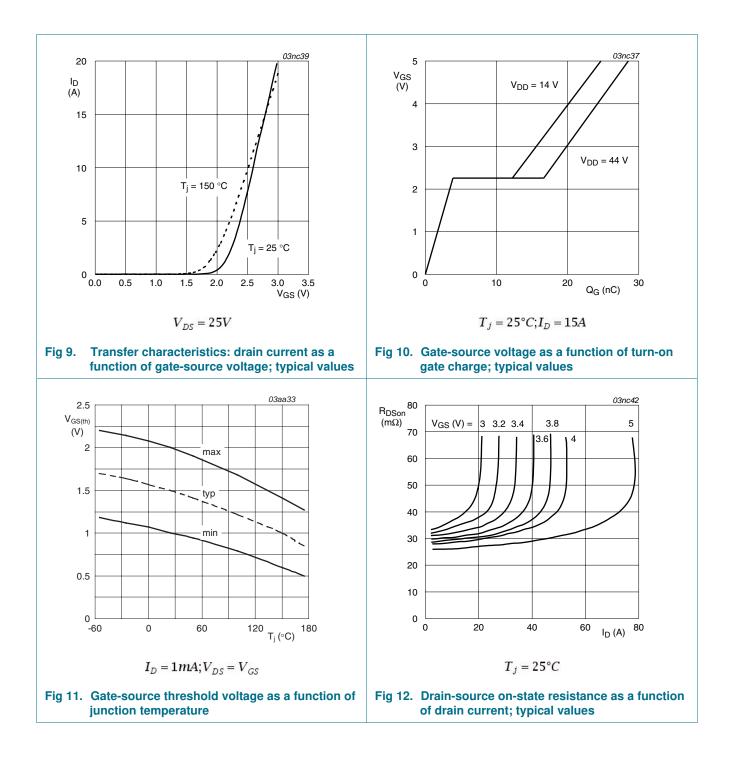
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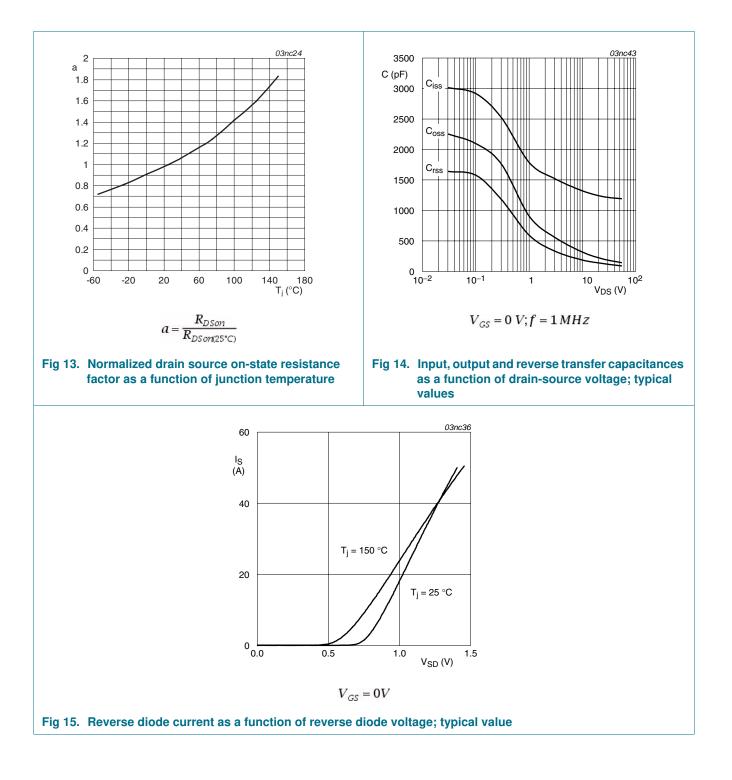
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7. Package outline

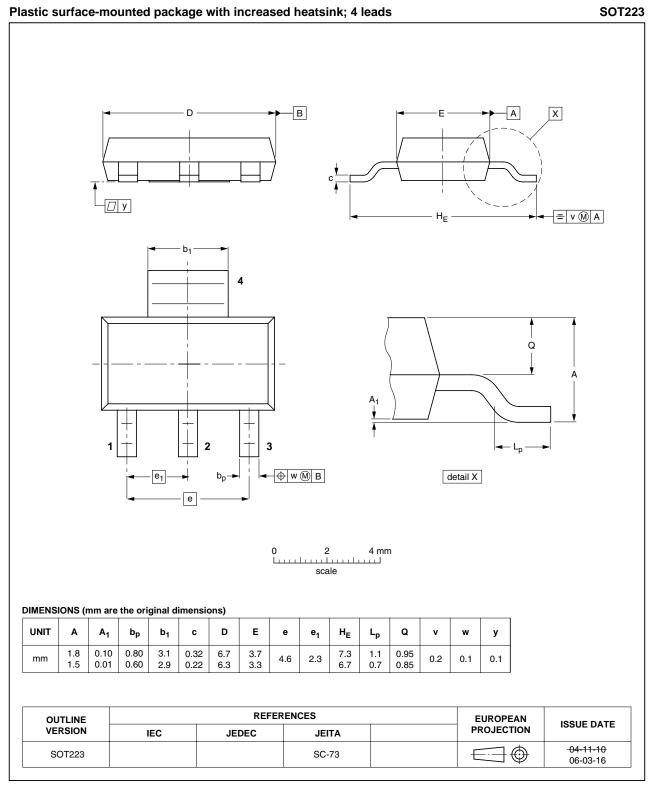


Fig 16. Package outline SOT223 (SC-73)

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9832-55A v.2	20100601	Product data sheet	-	BUK9832-55A-01
Modifications:	of NXP Se	miconductors.	en redesigned to comply ne new company name w	with the new identity guidelines here appropriate.
BUK9832-55A-01 (9397 750 07734)	20010131	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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